Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	-450	V
Gate-Source Voltage		V_{GSS}	±30	V
Continuous Drain Current (Note 5) V_{GS} =- 10V	T_C = +25°C T_C = +70°C	I_D	-0.25 -0.20	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I_{DM}	-0.45	A
Maximum Body Diode Continuous Current		I_S	-0.45	A
Avalanche Energy (Note 6) L=60mH		E_{AS}	4	mJ
Avalanche Current (Note 6) L=60mH		I_{AS}	0.25	A
Peak Diode Recovery dv/dt ($I_{SD} \leq$ 1.0A, di/dt $\leq$ 100A/µs)		dv/dt	4.5	V/ns

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)	T_C = +25°C	P_D	13.9	W
	T_C = +70°C		8.9	°C/W
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	59.4	W
Thermal Resistance, Junction to Case	(Note 6)	$R_{\theta JC}$	8.9	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)						
Drain-Source Breakdown Voltage	BV_{DSS}	-450	—	—	V	V_{GS} = 0V, I_D = -250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-1	µA	V_{DS} = -450V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±30V, V_{DS} = 0V
ON CHARACTERISTICS (Note 5)						
Gate Threshold Voltage	$V_{GS(TH)}$	-2.0	-3.0	-4.0	V	V_{DS} = V_{GS}, I_D = -250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	40	150	Ω	V_{GS} = -10V, I_D = -50mA
Diode Forward Voltage	V_{SD}	—	-0.8	-1.2	V	V_{GS} = 0V, I_S = -50mA
DYNAMIC CHARACTERISTICS (Note 6)						
Input Capacitance	C_{ISS}	—	59.2	—	pF	V_{DS} = -25V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{OSS}	—	11	—		
Reverse Transfer Capacitance	C_{RSS}	—	1	—		
Forward Transconductance	g_{FS}	40	—	—	ms	V_{DS}=-25V,I_D=-50mA
Gate Resistance	R_G	—	50	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz
Total Gate Charge	Q_G	—	1.8	—	nC	V_{DS} = -225V, I_D = -100mA, V_{GS} = -10V
Gate-Source Charge	Q_{GS}	—	0.3	—		
Gate-Drain Charge	Q_{GD}	—	0.9	—		
Turn-On Delay Time	$t_{D(ON)}$	—	12	—	ns	V_{DD}= -225V, R_G = 3.0Ω, I_D = -100mA
Turn-On Rise Time	t_R	—	9	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	19	—		
Turn-Off Fall Time	t_F	—	87	—		
Body Diode Reverse Recovery Time	t_{RR}	—	108	—	ns	V_{GS} = 0V, I_S = -100mA,V_{DD}=-100V, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q_{RR}	—	391	—	nC	V_{GS}= 0V, I_S=-100mA, V_{DD}=-100V ,di/dt = 100A/µs

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1 inch square copper pad layout.
6. Guaranteed by design. Not subject to production testing.

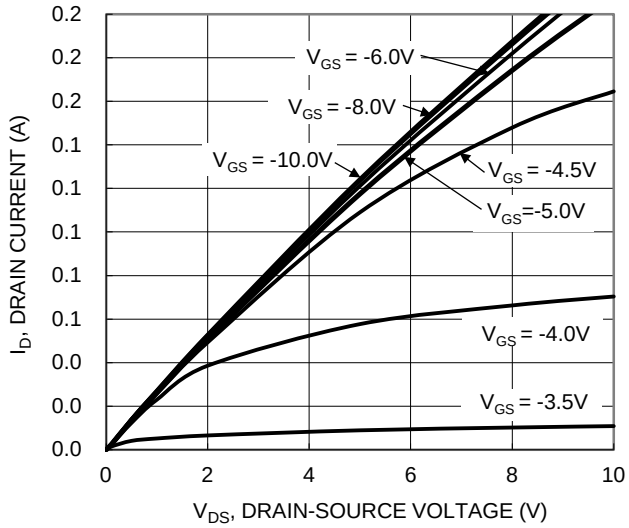


Figure 1.Typical Output Characteristic

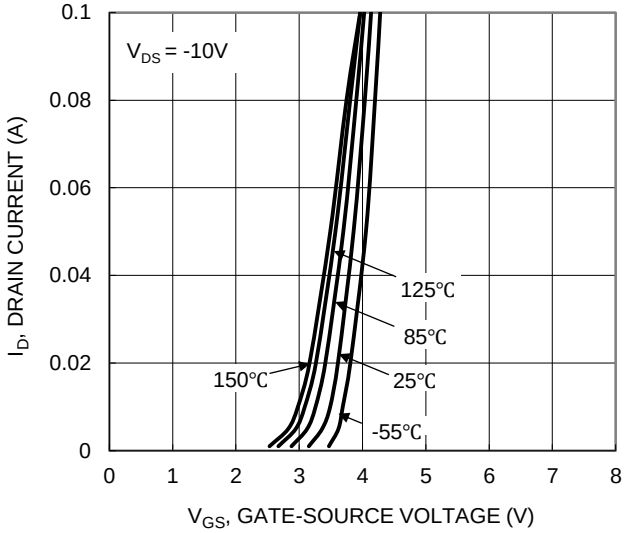


Figure 2. Typical Transfer Characteristic

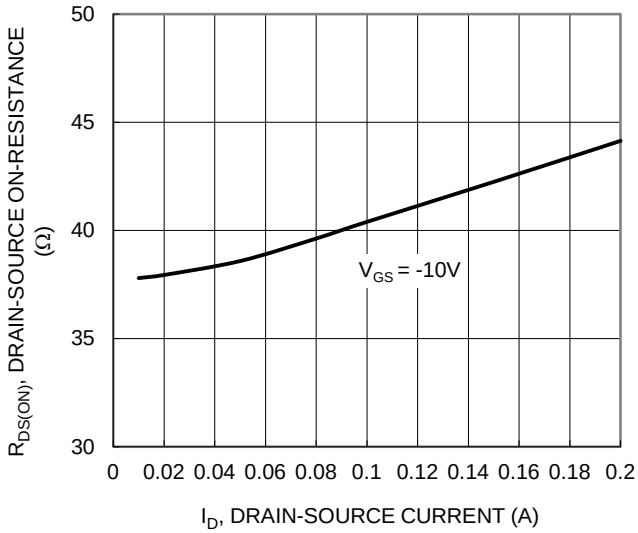


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

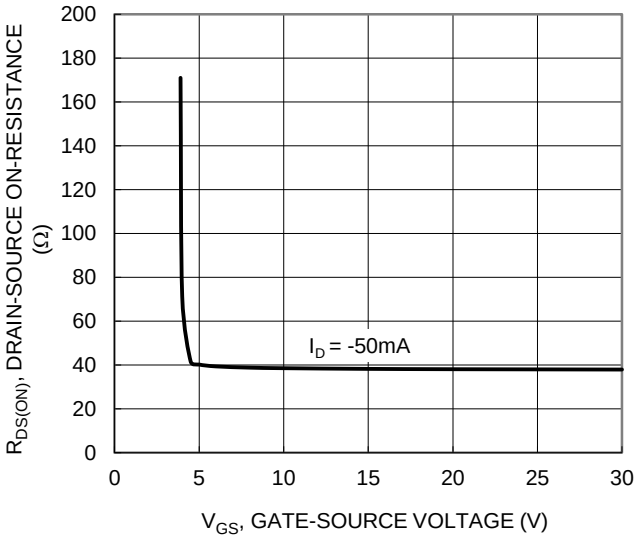


Figure 4. Typical Transfer Characteristic

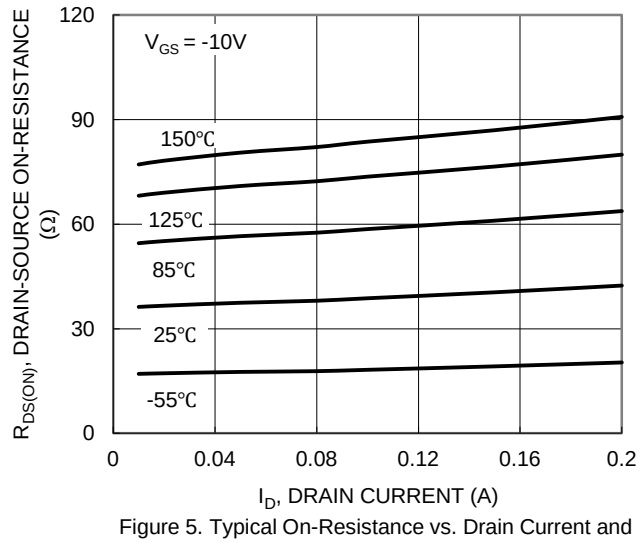


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

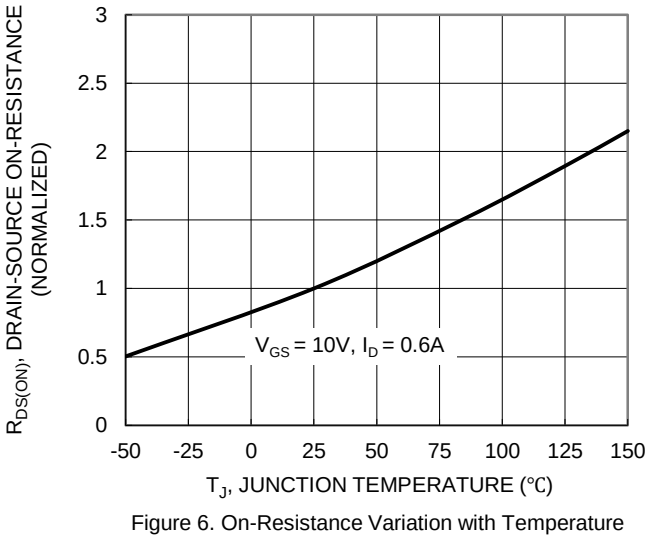


Figure 6. On-Resistance Variation with Temperature

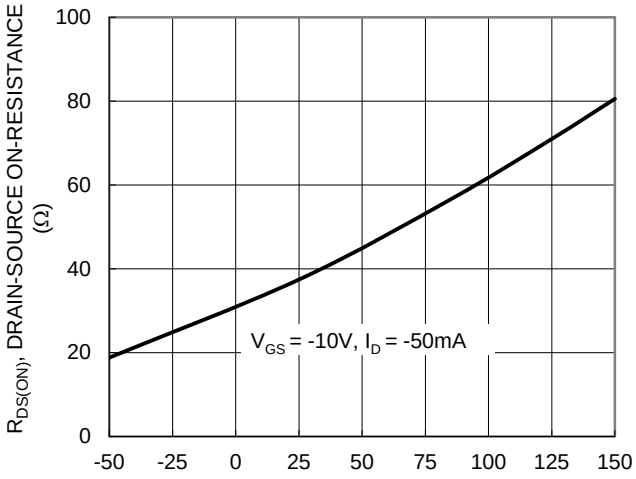


Figure 7. On-Resistance Variation with Temperature

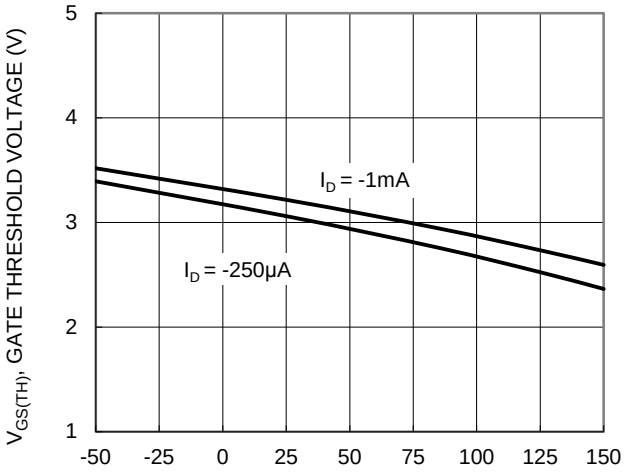


Figure 8. Gate Threshold Variation vs. Junction Temperature

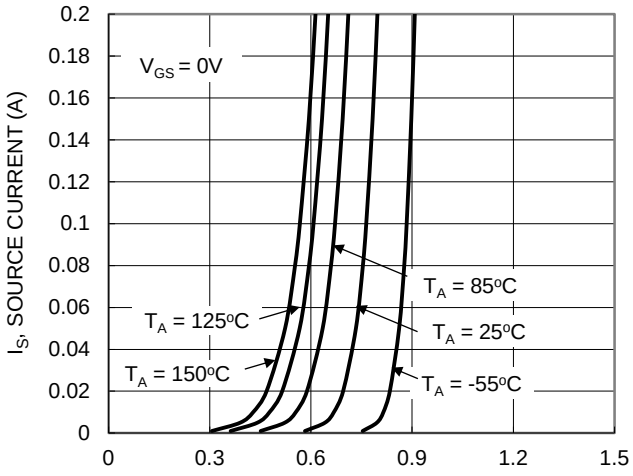


Figure 9. Diode Forward Voltage vs. Current

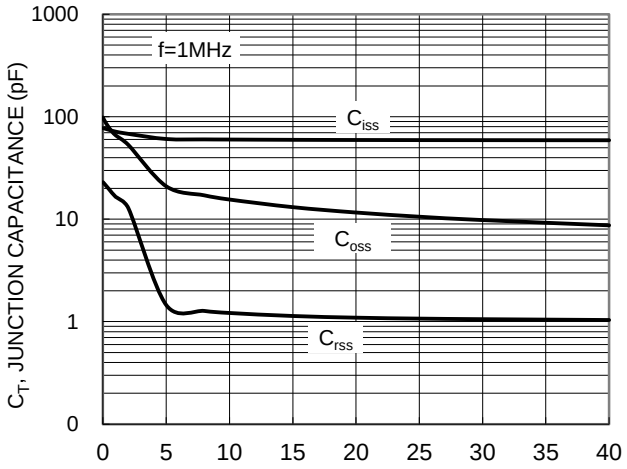


Figure 10. Typical Junction Capacitance

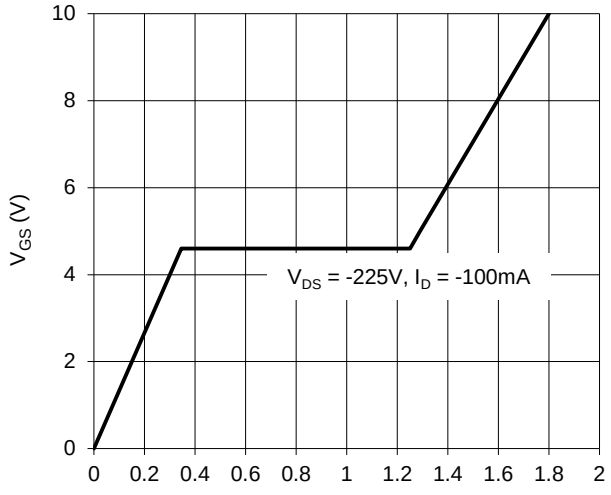


Figure 11. Gate Charge

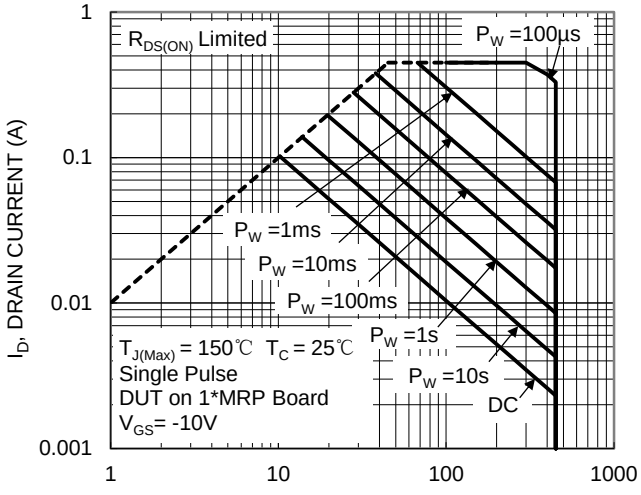
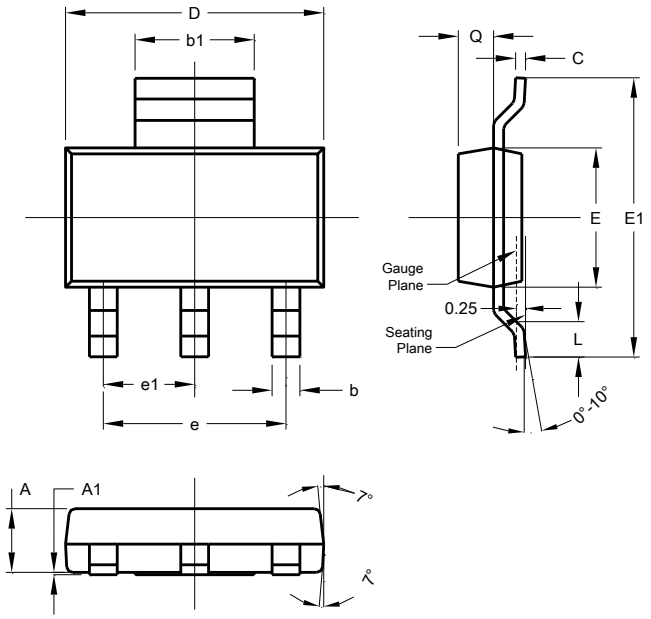


Figure 12. SOA, Safe Operation Area

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223

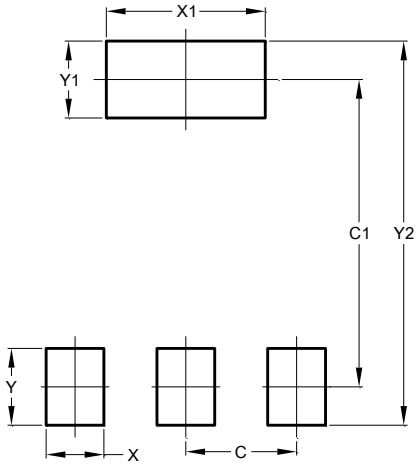


SOT223			
Dim	**Min**	**Max**	**Typ**
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b	0.60	0.80	0.70
b1	2.90	3.10	3.00
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	-	-	4.60
e1	-	-	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

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